

HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

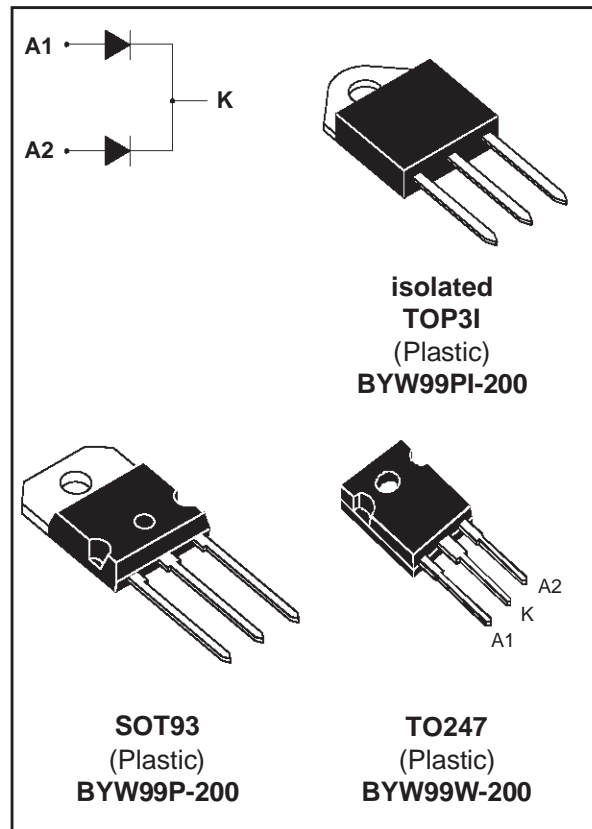
FEATURES

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- INSULATED VERSION TOP3I :
Insulating voltage = 2500 V DC
Capacitance = 12 pF

DESCRIPTION

Dual center tap rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged in SOT93, TOP3I or TO247 this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | | | Value | Unit |
|--------------------|---|---------------|---------------------------------|--------------------------------|--------------------------------------|
| $I_{F(RMS)}$ | RMS forward current | | | 35 | A |
| $I_{F(AV)}$ | Average forward current $\delta = 0.5$ | SOT93 / TO247 | $T_c=120^\circ\text{C}$ | 15 | A |
| | | TOP3I | $T_c=115^\circ\text{C}$ | 15 | |
| I_{FSM} | Surge non repetitive forward current | | $t_p=10\text{ms}$ sinusoidal | 200 | A |
| T_{stg} T_j | Storage and junction temperature range | | | - 40 to + 150 - 40 to + 150 | $^\circ\text{C}$ $^\circ\text{C}$ |

| Symbol | Parameter | Value | Unit |
|-----------|---------------------------------|-------|------|
| V_{RRM} | Repetitive peak reverse voltage | 200 | V |

BYW99P/PI/W**THERMAL RESISTANCES**

| Symbol | Parameter | | | Value | Unit |
|-----------|------------------|---------------|-----------|-------|------|
| Rth (j-c) | Junction to case | SOT93 / TO247 | Per diode | 1.8 | °C/W |
| | | | Total | 1.0 | |
| | | TOP3I | Per diode | 2.0 | |
| | | | Total | 1.25 | |
| Rth (c) | Coupling | SOT93 / TO247 | | 0.2 | °C/W |
| | | TOP3I | | 0.5 | |

When the diodes 1 and 2 are used simultaneously :

$$T_j - T_c (\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)} (\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (Per diode)

| Symbol | Test Conditions | | Min. | Typ. | Max. | Unit |
|-------------------|------------------------|-----------------------------------|------|------|------|------|
| I _R * | T _j = 25°C | V _R = V _{RRM} | | | 20 | μA |
| | T _j = 100°C | | | | 1.5 | mA |
| V _F ** | T _j = 125°C | I _F = 12 A | | | 0.85 | V |
| | T _j = 125°C | I _F = 25 A | | | 1.05 | |
| | T _j = 25°C | I _F = 25 A | | | 1.15 | |

Pulse test : * tp = 5 ms, δ < 2 %

** tp = 380 μs, δ < 2 %

To evaluate the conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.016 \times I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

| Symbol | Test Conditions | | Min. | Typ. | Max. | Unit |
|-----------------|-----------------------|---|------|-------------------------------|------|------|
| trr | T _j = 25°C | I _F = 0.5A I _R = 1A | | | 25 | ns |
| | | I _F = 1A V _R = 30V | | dI _F /dt = -50A/μs | 40 | |
| tfr | T _j = 25°C | I _F = 1A V _{FR} = 1.1 x V _F | | 15 | | ns |
| V _{FP} | T _j = 25°C | I _F = 1A | | 2 | | V |

Fig.1 : Average forward power dissipation versus average forward current.

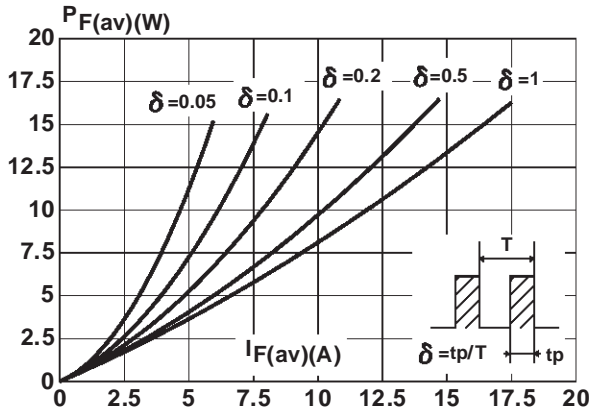


Fig.2 : Peak current versus form factor.

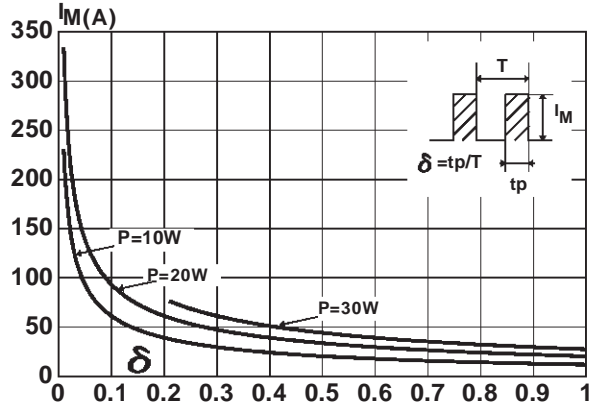


Fig.3 : Forward voltage drop versus forward current (maximum values).

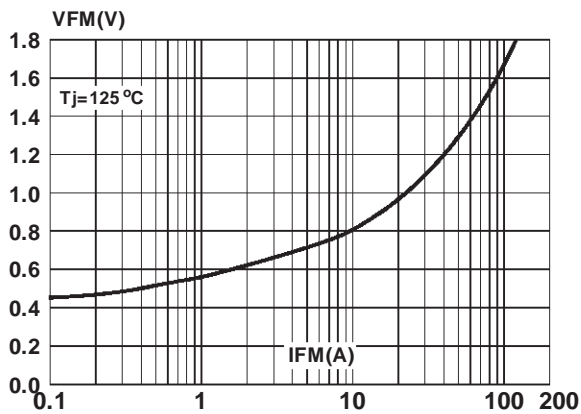


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

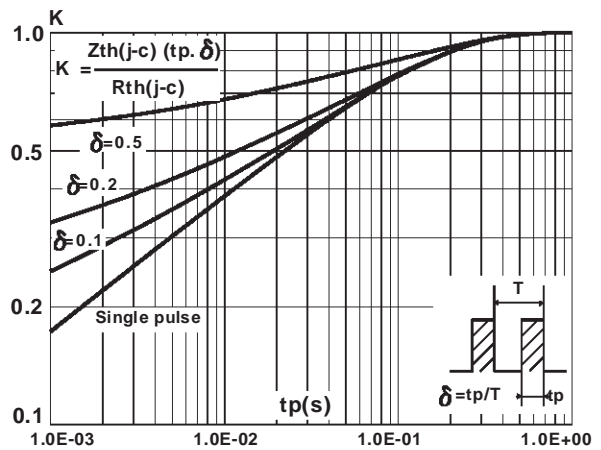


Fig.5 : Non repetitive surge peak forward current versus overload duration. (SOT93, TO247)

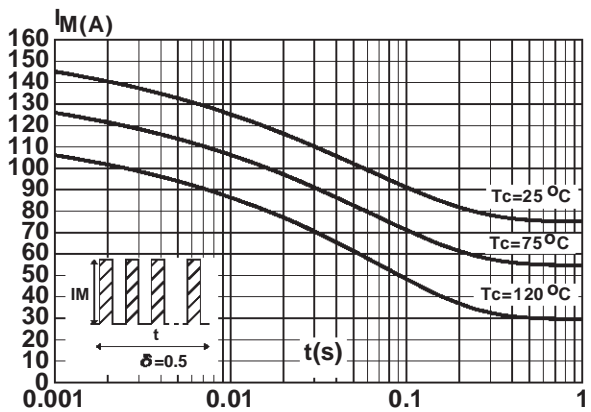


Fig.6 : Non repetitive surge peak forward current versus overload duration. (TOP31)

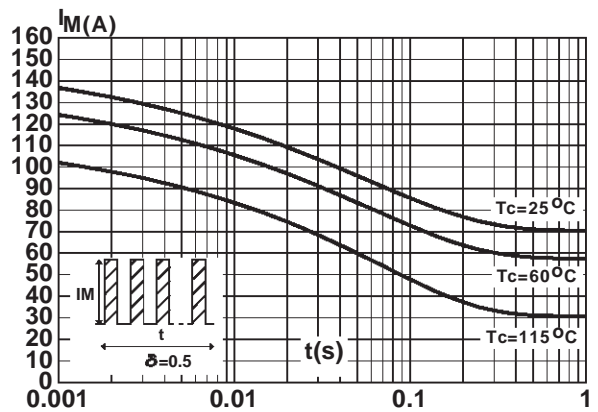


Fig.7 : Average current versus ambient temperature.
($\delta = 0.5$) (SOT93, TO247)

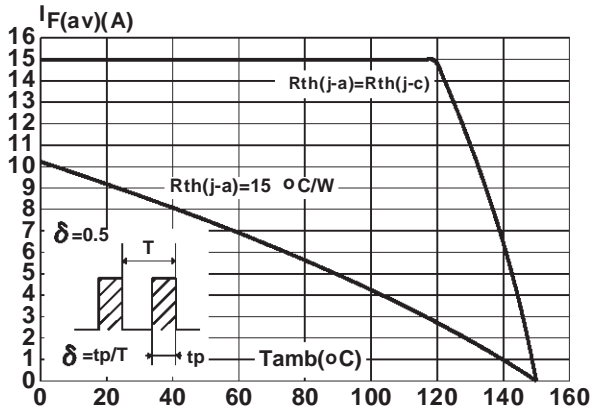


Fig.8 : Average current versus ambient temperature.
($\delta = 0.5$) (TOP3I)

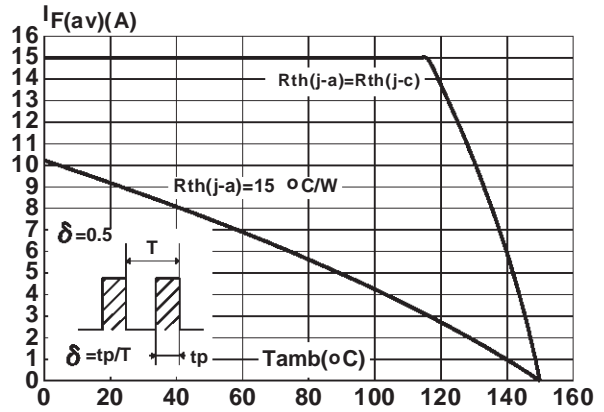


Fig.9 : Junction capacitance versus reverse voltage applied (Typical values).

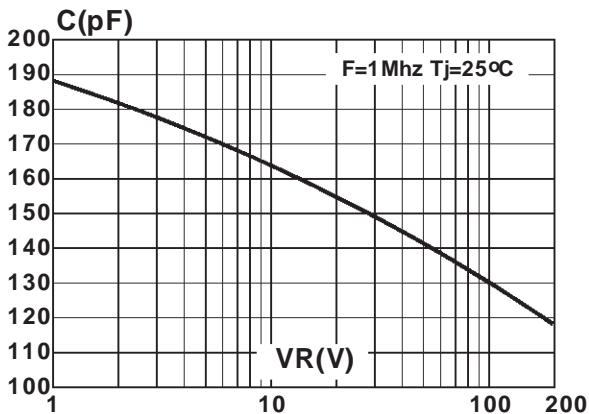


Fig.10 : Recovery charges versus dI_F/dt .

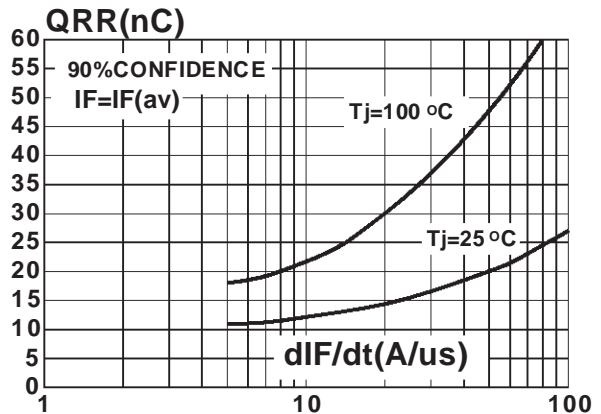


Fig.11 : Peak reverse current versus dI_F/dt .

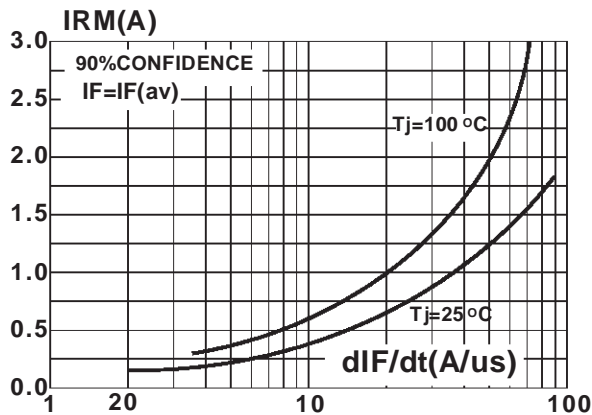
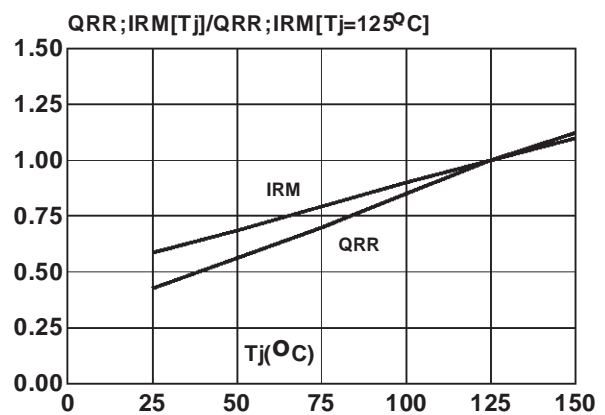
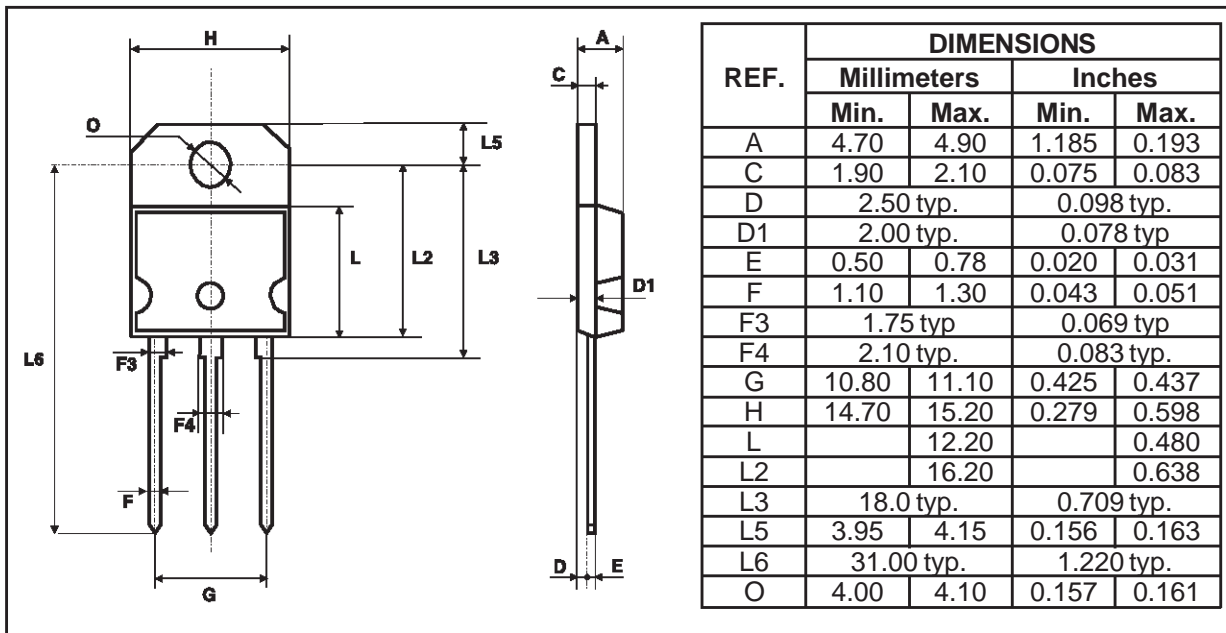


Fig.12 : Dynamic parameters versus junction temperature.

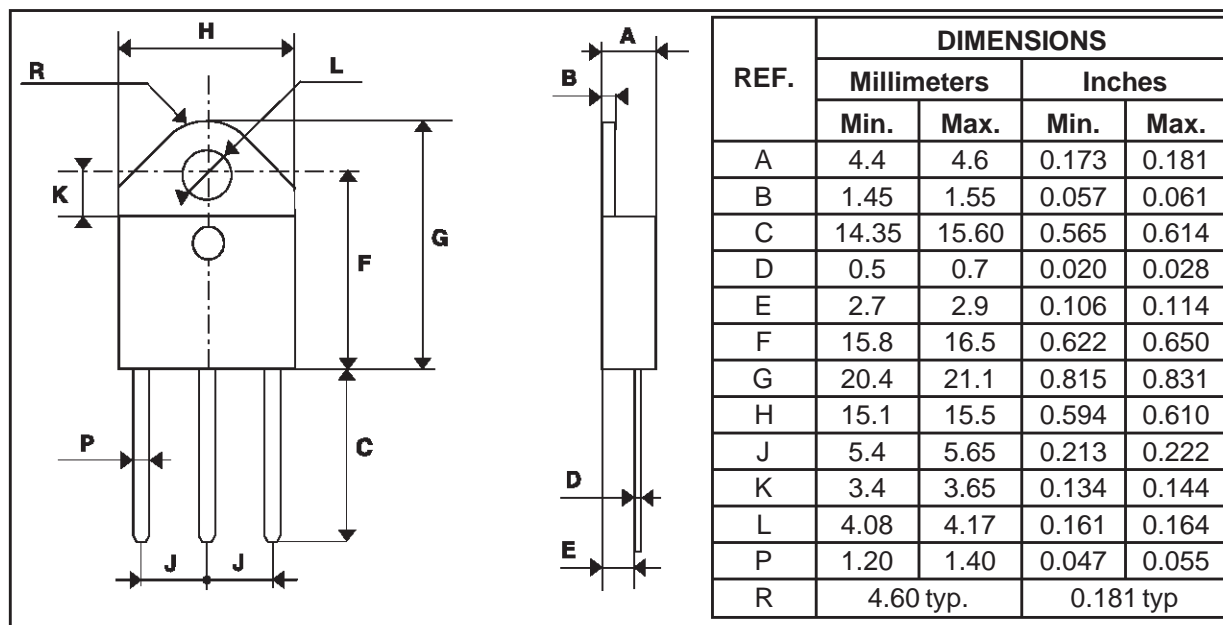


PACKAGE MECHANICAL DATA
SOT93



- **Marking** : Type number
- Cooling method : C
- Weight : 5.3 g
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N

PACKAGE MECHANICAL DATA
TOP3I (isolated)

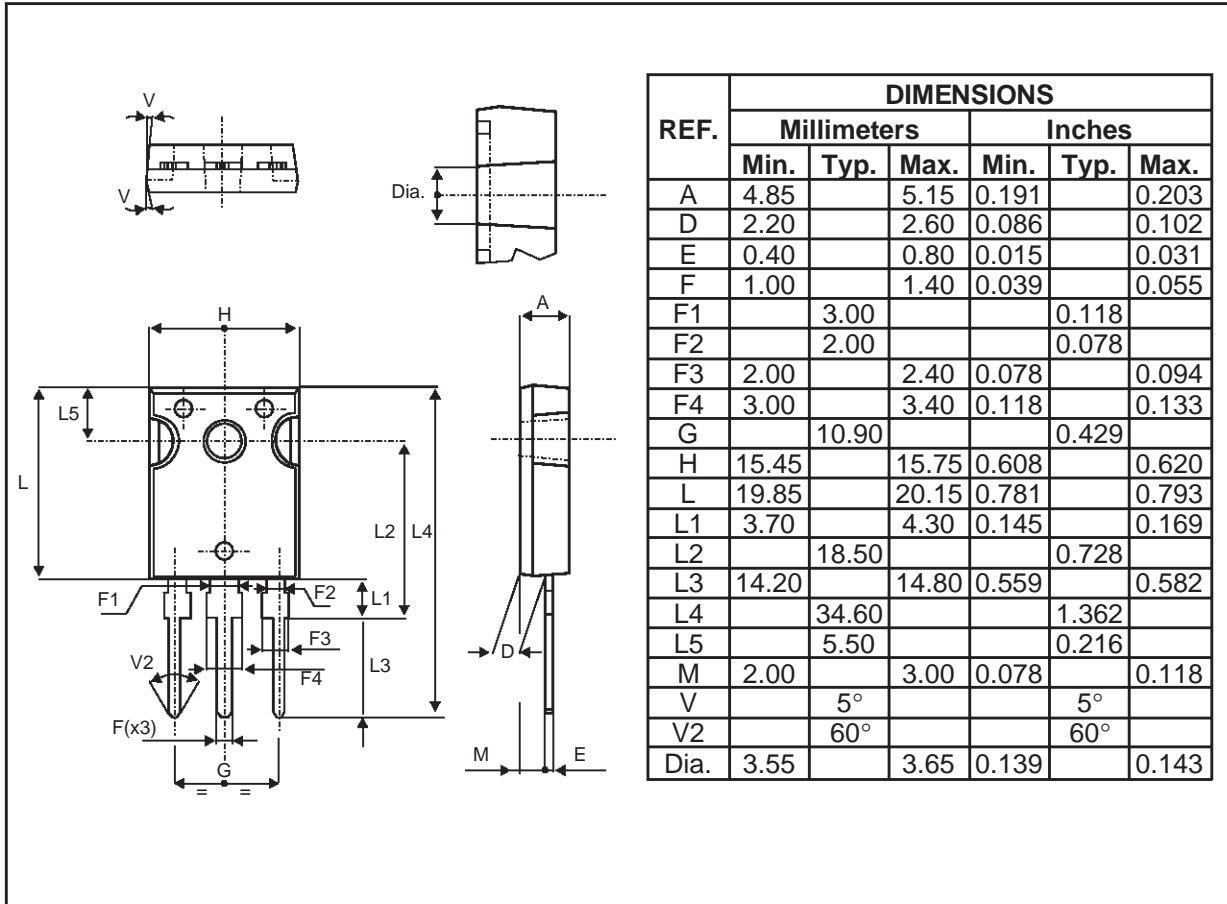


- **Marking** : Type number
- Cooling method : C
- Weight : 4.7 g
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N



BYW99P/PI/W

PACKAGE MECHANICAL DATA TO247



- **Marking** : Type number
- **Cooling method** : C
- **Weight** : 4.4 g
- **Recommended torque value** : 0.8m.N
- **Maximum torque value** : 1.0m.N

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